

**AMENDMENTS TO THE CLAIMS:**

**Please cancel claims 3 - 5 without prejudice or disclaimer, and amend the claims as follows:**

1. (Currently Amended) A III group nitride system compound semiconductor light emitting element, comprising:

a transparent substrate that ~~is of~~ comprises a material ~~except for other than a~~ III group nitride system compound semiconductor;

a convex light trapping member that is formed over ~~directly or through a buffer layer on the~~ a surface of the transparent substrate; and

a III group nitride system compound semiconductor layer that is formed on the surface of the transparent substrate;

wherein the light trapping member has a refractive index substantially equal to ~~that a~~ refractive index of the transparent substrate or closer to ~~that the refractive index~~ of the transparent substrate than ~~that a refractive index~~ of the III group nitride system compound semiconductor layer.

2. (Currently Amended) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein:

the transparent substrate ~~is of~~ comprises sapphire, and

the light trapping member ~~is of~~ comprises at least one ~~selected from the group of~~  $\text{Al}_2\text{O}_3$ ,  $\text{Eu}_2\text{O}_3$ ,  $\text{La}_2\text{O}_3$ ,  $\text{Sm}_2\text{O}_3$ ,  $\text{WO}_3$  and  $\text{Y}_2\text{O}_3$ .

3-5. (Canceled)

6. (Currently Amended) A pretreated transparent substrate, comprising:

a transparent substrate that ~~is of~~ comprises a material ~~except for other than~~ III group nitride system compound semiconductor; and

a convex light trapping member that is formed over ~~directly or through a buffer layer~~

~~on the~~ a surface of the transparent substrate;

wherein the light trapping member has a refractive index substantially equal to ~~that a~~ refractive index of the transparent substrate or closer to ~~that~~ the refractive index of the transparent substrate than ~~that a refractive index of the~~ a III group nitride system compound semiconductor ~~layer~~.

7. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member is formed directly on the surface of the transparent substrate.

8. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, further comprising:

a buffer layer disposed on the surface of said transparent substrate,

wherein said convex light trapping member is formed on the buffer layer such that the buffer layer is disposed between said convex light trapping member and said transparent substrate.

9. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member comprises an uneven pattern formed on an entirety of the surface of the substrate.

10. (New) The III group nitride system compound semiconductor light emitting element according to claim 8, wherein said buffer layer comprises at least one of AlN, GaN, InN, AlGaN, InGaN and AlInGaN.

11. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member comprises:

inclined side portions; and

a top portion positioned between said inclined side portions.

12. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein a light component projecting onto a top surface of the convex light trapping member at an incident angle of more than approximately 47 degrees is subjected to total reflection, and

wherein other light components are trapped into the convex light trapping member and the transparent substrate and are discharged outside of the transparent substrate.

13. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein light entering into said convex light trapping member is directly transmitted through said transparent substrate and then discharged outside of said substrate.

14. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member is formed independently from said transparent substrate.

15. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein said convex light trapping member comprises a width of  $0.1\mu\text{m}$  to  $10\mu\text{m}$ , a pitch of  $0.2\mu\text{m}$  to  $20\mu\text{m}$  and a height of  $0.1\mu\text{m}$  to  $5\mu\text{m}$ .

16. (New) The pretreated transparent substrate according to claim 6, wherein:

the transparent substrate comprises sapphire, and

the light trapping member comprises at least one of  $\text{Al}_2\text{O}_3$ ,  $\text{Eu}_2\text{O}_3$ ,  $\text{La}_2\text{O}_3$ ,  $\text{Sm}_2\text{O}_3$ ,  $\text{WO}_3$  and  $\text{Y}_2\text{O}_3$ .

17. (New) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member is formed directly on the surface of the transparent substrate.

18. (New) The pretreated transparent substrate according to claim 6, further comprising:

a buffer layer disposed on the surface of said transparent substrate,  
wherein said convex light trapping member is formed on the buffer layer such that the buffer layer is disposed between said convex light trapping member and said transparent substrate.

19. (New) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member comprises an uneven pattern formed on an entirety of the surface the substrate.

20. (New) The pretreated transparent substrate according to claim 6, wherein said convex light trapping member comprises:

inclined side portions; and

a top portion positioned between said inclined side portions.

21. (New) The pretreated transparent substrate according to claim 6, wherein a light component projecting onto a top surface of the convex light trapping member at an incident angle of more than approximately 47 degrees is subjected to total reflection, and

wherein other light components are trapped into the convex light trapping member and the transparent substrate and are discharged outside of the transparent substrate.

22. (New) A light emitting diode, comprising:

a III group nitride system compound semiconductor light emitting element,  
comprising:

a transparent substrate that comprises a material other than a III group nitride system compound semiconductor;

a convex light trapping member that is formed over a surface of the transparent substrate; and

a III group nitride system compound semiconductor layer that is formed on the surface of the transparent substrate,

wherein the light trapping member has a refractive index substantially equal to a refractive index of the transparent substrate or closer to the refractive index of the transparent substrate than a refractive index of the III group nitride system compound semiconductor layer.

23. (New) A method of forming a III group nitride system compound semiconductor light emitting element comprising:

providing a transparent substrate comprising a material other than a III group nitride system compound semiconductor;

laminating a layer for a convex light trapping member over a surface of the transparent substrate;

forming a photomask over said layer for said convex light trapping member; and  
etching and removing an exposed portion of said layer for said convex light trapping member,

wherein said light trapping member has a refractive index substantially equal to a refractive index of the transparent substrate or closer to the refractive index of the transparent substrate than a refractive index of the III group nitride system compound semiconductor layer.

24. (New) The III group nitride system compound semiconductor light emitting element according to claim 1, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.

25. (New) The pretreated transparent substrate according to claim 6, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.

26. (New) The light emitting diode according to claim 22, wherein light entering into said light emitting member is directly transmitted through the transparent substrate.